DATA SHEET

NE/SA5521
LVDT signal conditioner

Product data
Supersedes data of 1994 Aug 31

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Philips
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LVDT signal conditioner NE/SA5521

DESCRIPTION

The NE/SA5521 is a signal conditioning circuit for use with Linear Variable Differential Transformers (LVDTs) and Rotary Variable Differential Transformers (RVDTs). The chip includes a low distortion, amplitude-stable sine wave oscillator with programmable frequency to drive the primary of the LVDT/RVDT, a synchronous demodulator to convert the LVDT/RVDT output amplitude and phase to position information, and an output amplifier to provide amplification and filtering of the demodulated signal.

FEATURES

- Low distortion
- Single supply 5 V to 20 V, or dual supply ±2.5 V to ±10 V
- Oscillator frequency 1 kHz to 20 kHz
- Capable of ratiometric operation
- Low power consumption (182 mV typ)

APPLICATIONS

- LVDT signal conditioning
- RVDT signal conditioning
- LPDT signal conditioning
- Bridge circuits

PIN CONFIGURATIONS

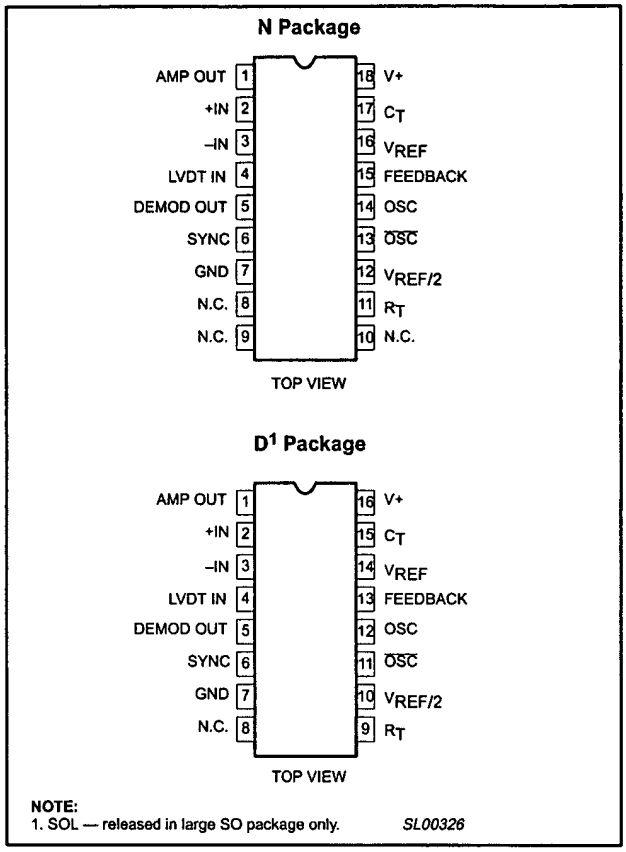


Figure 1. Pin configurations

ORDERING INFORMATION

ORDER CODE	DESCRIPTION	TEMPERATURE RANGE	DWG #
NE5521D	16-Pin Small Outline Large (SOL) Package	0 °C to +70 °C	SOT162-1
NE5521N	18-Pin Plastic Dual In-Line Package (DIP)	0 °C to +70 °C	SOT102-4
SA5521D	16-Pin Small Outline Large (SOL) Package	–40 °C to +85 °C	SOT162-1
SA5521N	18-Pin Plastic Dual In-Line Package (DIP)	–40 °C to +85 °C	SOT102-4

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_{CC}	Supply voltage	+20	V
	Split supply voltage	±10	V
T_{amb}	Operating temperature range NE5521 SA5521	 0 to 70 –40 to +85	 °C °C
T_{stg}	Storage temperature range	–65 to +125	°C
P_D	Power dissipation[1]	910	mW

NOTES:
1. For derating, see typical power dissipation versus load curves (Figure 3).

BLOCK DIAGRAM

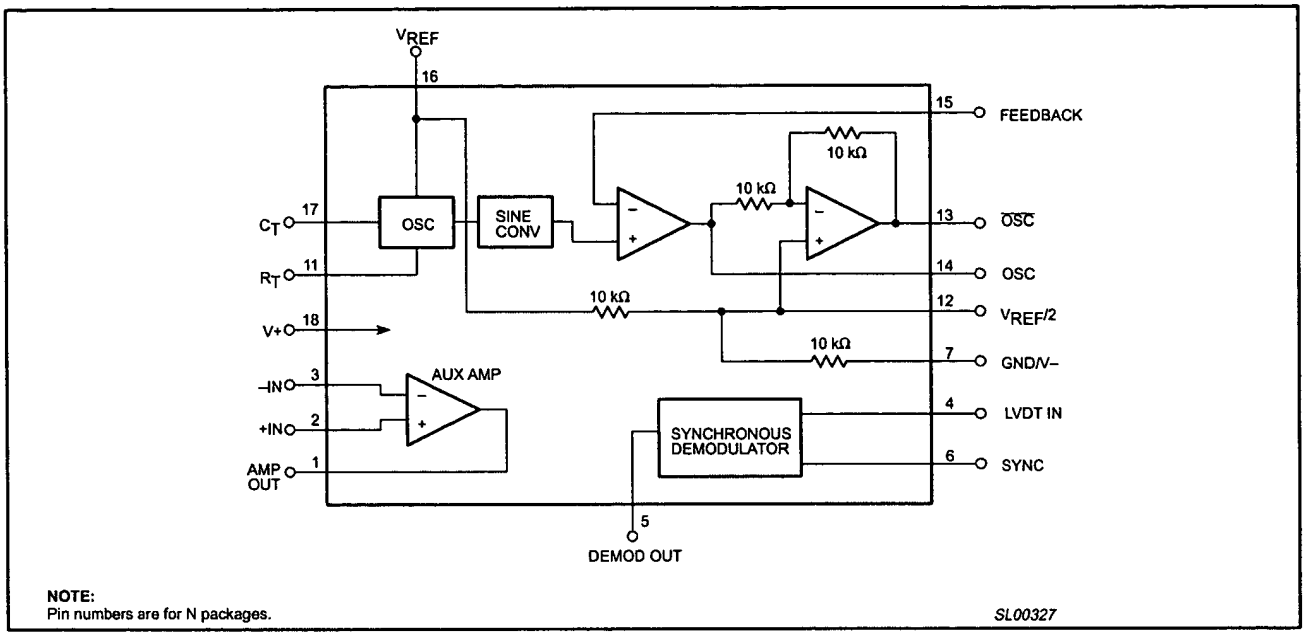


Figure 2. Block diagram.

PIN DEFINITIONS FOR D AND N PACKAGES

PIN NO.		SYMBOL	DEFINITION
D	N		
1	1	Amp Out	Auxiliary Amplifier Out.
2	2	+IN	Auxiliary Amplifier non-inverting input.
3	3	–IN	Auxiliary Amplifier inverting input.
4	4	LVDT IN	Input to Synchronous Demodulator from the LVDT/RVDT secondary.
5	5	DEMOD OUT	Pulsating DC output from the Synchronous Demodulator output. This voltage should be filtered before use.
6	6	SYNC	Synchronizing input for the Synchronizing Demodulator. This input should be connected to the OSC or $\overline{OSC}$ output. Sync is referenced to $V_{REF}/2$.
7	7	GND	Device return. Should be connected to system ground or to the negative supply.
8	8	NC	No internal connection.
--	9	NC	No internal connection.
--	10	NC	No internal connection.
9	11	R_T	A temperature stable 18 kΩ resistor should be connected between this pin and Pin 7.
10	12	$V_{REF}/2$	A high impedance source of one half the potential applied to V_{REF}. The LVDT/RVDT secondary return should be to this point. A bypass capacitor with low impedance at the oscillator frequency should also be connected between this pin and ground.
11	13	$\overline{OSC}$	Oscillator sine wave output that is 180° out of phase with the OSC signal. The LVDT/RVDT primary is usually connected between OSC and $\overline{OSC}$ pins.
12	14	OSC	Oscillator sine wave output. The LVDT/RVDT primaries are usually connected between OSC and $\overline{OSC}$ pins.
13	15	FEEDBACK	Usually connected to the OSC output for unity gain, a resistor between this pin and OSC, and one between this pin and ground can provide for a change in the oscillator output pin amplitudes.
14	16	V_{REF}	Reference voltage input for the oscillator and sine converter. This voltage MUST be stable and must not exceed +V supply voltage.
15	17	C_T	Oscillator frequency-determining capacitor. The capacitor connected between this pin and ground should be a temperature-stable type.
16	18	+V	Positive supply connection.

DC ELECTRICAL CHARACTERISTICS

$V+ = V_{REF}$ = 10 V; T_{amb} = 0 °C to 70 °C for NE5521, T_{amb} = –40 °C to 85 °C for SA5521; Frequency = 1 kHz, unless otherwise noted.

SYMBOL	PARAMETER	TEST CONDITIONS	NE5521			SA5521			UNIT
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	Supply current			12.9	20		12.9	18	mA
I_{REF}	Reference current			5.3	8		5.3	8	mA
V_{REF}	Reference voltage range		5		V+	5		V+	V
P_D	Power dissipation			182	280		182	260	mW
Oscillator Section									
	Oscillator output	R_L = 10 kΩ	$\frac{V_{REF}}{8.8}$				$\frac{V_{REF}}{8.8}$		V_{RMS}
THD	Sine wave distortion	No load		1.5			1.5		%
	Initial amplitude error	T_{amb} = 25 °C		0.4	±3		0.4	±3	%
	Tempco of amplitude			0.005	0.01		0.005	0.01	%/°C
	Init. accuracy of oscillator freq.	T_{amb} = 25 °C		±0.9	±5		±0.9	±5	%
	Temperature coeff. of frequency[1]			0.05			0.05		%/°C
	Voltage coeff. of frequency			2.5			3.3		%/V(V_{REF})
	Min OSC ($\overline{OSC}$) Load[2]		300	170		300	170		Ω
Demodulator Section									
ϵ_r	Linearity error	5 V_{P-P} input		±0.05	±0.1		±0.05	±0.1	%FS
	Maximum demodulator input			$\frac{V_{REF}}{2}$			$\frac{V_{REF}}{2}$		V_{P-P}
V_{OS}	Demodulator offset voltage			±1.4	±5		±1.4	±5	mV
TCV_{OS}	Demodulator offset voltage drift			5	25		5	25	µV/°C
I_{BIAS}	Demodulator input current		–600	–234		–500	–234		nA
	$V_{R/2}$ accuracy			±0.1	±1		±0.1	±1	%
Auxiliary Output Amplifier									
V_{OS}	Input offset voltage			±0.5	±5		±0.5	±5	mV
I_{BIAS}	Input bias current		–600	–210		–500	–210		nA
I_{OS}	Input offset current			10	50		10	50	nA
A_V	Gain		100	385		100	385		V/mV
SR	Slew rate			1.3			1.3		V/µs
GBW	Unity gain bandwidth product	A_V = 1		1.6			1.6		MHz
	Output voltage swing	R_L = 10 kΩ	7	8.2		7	8.2		V
	Output short circuit current to ground or to V_{CC}	T_{amb} = 25 °C		42	100		42	100	mA

NOTES:

1. This is temperature coefficient of frequency for the device only. It is assumed that C_T and R_T are fixed in value and C_T leakage is fixed over the operating temperature range.
2. Minimum load impedance for which distortion is guaranteed to be less than 5%.

DEFINITION OF TERMS

TERM	DEFINITION
Oscillator output	RMS value of the AC voltage at the oscillator output pin. This output is referenced to $V_{REF/2}$ and is a function of V_{REF}.
Sine wave distortion	The Total Harmonic Distortion (THD) of the oscillator output with no load. This is not a critical specification in LVDT/RVDT systems. This figure could be 15% or more without affecting system performance.
Initial amplitude error	A measure of the interchangeability of NE/SA5521 parts, not a characteristic of any one part. It is the degree to which the oscillator output of a number of NE/SA5521 samples will vary from the median of that sample.
Initial accuracy of oscillator frequency	Another measure of the interchangeability of individual NE/SA5521 parts. This is the degree to which the oscillator frequency of a number of NE/SA5521 samples will vary from the median of that sample with a given timing capacitor.
Tempco of oscillator amplitude	A measure of how the oscillator amplitude varies with ambient temperature as that temperature deviates from a 25 °C ambient.
Tempco of oscillator frequency	A measure of how the oscillator frequency varies with ambient temperature as that temperature deviates from a 25 °C ambient.
Voltage coefficient of oscillator frequency	The degree to which the oscillator frequency will vary as the reference voltage (V_{REF}) deviates from +10 V.
Min OSC ($\overline{OSC}$) load	Minimum load impedance for which distortion is guaranteed to be less than 5%.
Linearity error	The degree to which the DC output of the demodulator/amplifier combination matches a change in the AC signal at the demodulator input. It is measured as the worst case nonlinearity from a straight line drawn between positive and negative fullscale end points.
Maximum demodulator input	The maximum signal that can be applied to the demodulator input without exceeding the specified linearity error.

APPLICATION INFORMATION

$$\text{OSC frequency} = \frac{V_{REF} - 1.3V}{V_{REF}\,(R_T + 1.5k)\,C_T}$$

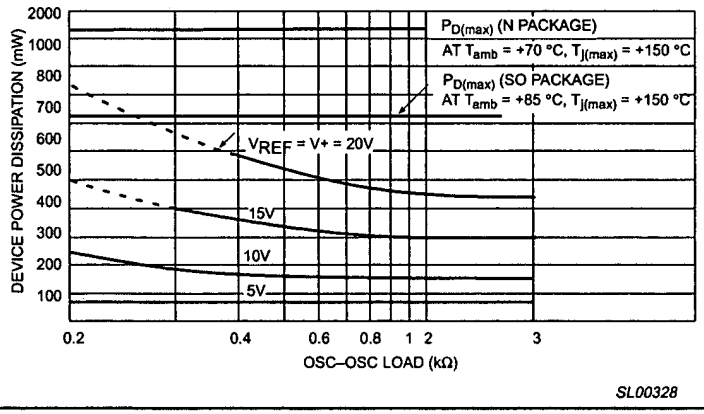


Figure 3. Device power dissipation versus OSC – $\overline{OSC}$ Load at +25 °C

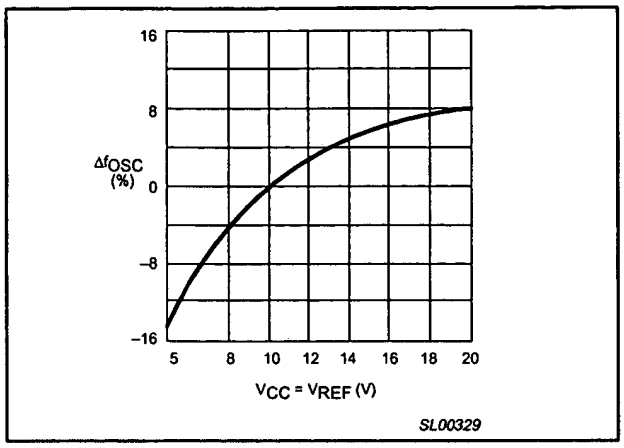


Figure 4. Oscillator frequency variation with voltage (Normalized to $V_{REF} = V_{CC} = 10$ V) $T_{amb} = +25$ °C

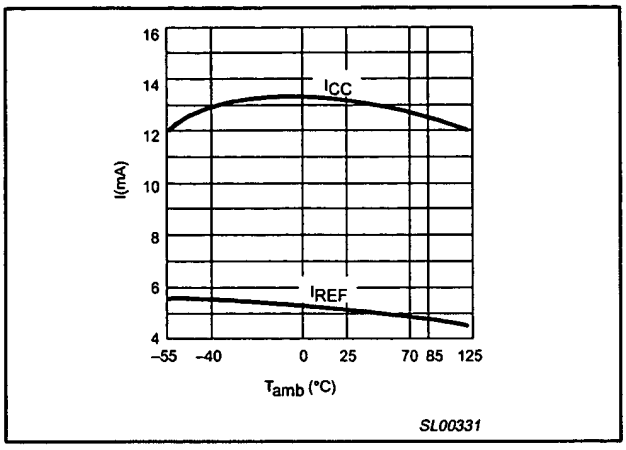


Figure 6. I_{REF} and I_{CC} versus Temperature ($V_{REF} = V_{CC} = 10$ V)

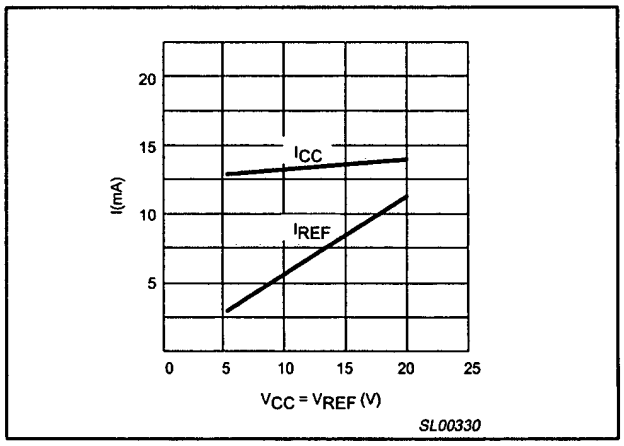
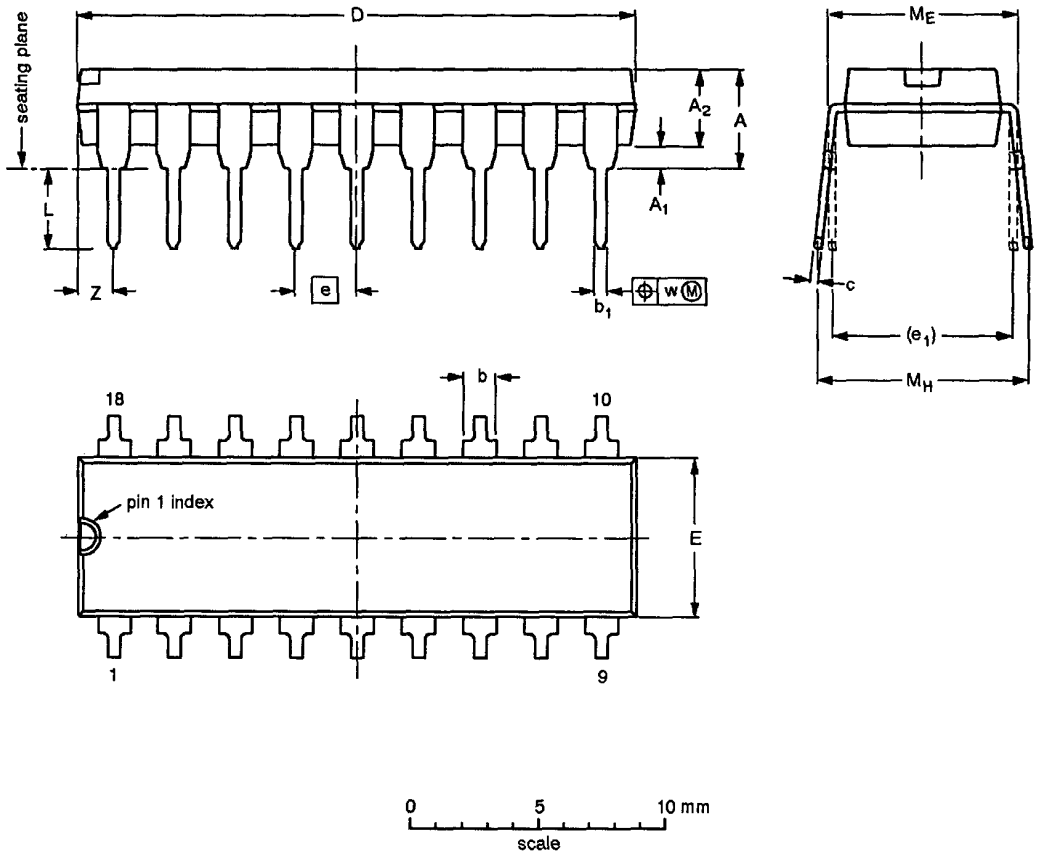


Figure 5. I_{REF} and I_{CC} versus voltage ($T_{amb} = +25$ °C)

DIP18: plastic dual in-line package; 18 leads (300 mil); long body **SOT102-4**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

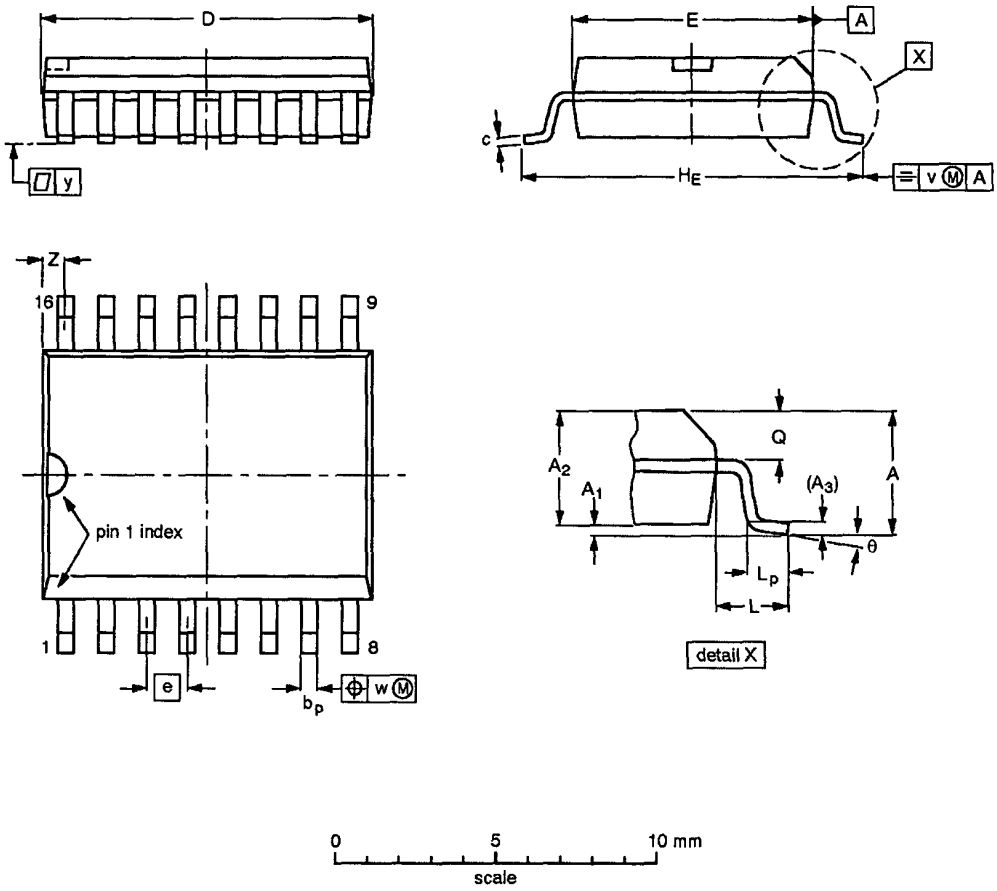
UNIT	A max.	A_1 min.	A_2 max.	b	b_1	c	$D^{(1)}$	$E^{(1)}$	e	e_1	L	M_E	M_H	w	$Z^{(1)}$ max.
mm	4.06	0.51	3.38	1.63 1.14	0.56 0.43	0.36 0.25	23.37 22.61	6.48 6.22	2.54	7.62	3.51 3.05	8.13 7.62	10.03 7.62	0.25	1.65
inches	0.160	0.020	0.140	0.064 0.045	0.022 0.017	0.014 0.010	0.920 0.890	0.255 0.245	0.100	0.300	0.138 0.120	0.32 0.30	0.395 0.300	0.01	0.065

Note

1. Plastic or metal protrusions of 0.01 inch maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT102-4		MS-001				~~99-07-08~~ 99-12-27

SO16: plastic small outline package; 16 leads; body width 7.5 mm SOT162-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	10.5 10.1	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.41 0.40	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT162-1	075E03	MS-013				~~97-05-22~~ 99-12-27

REVISION HISTORY

Rev	Date	Description
_2	20021105	**Product data; second version (9397 750 10666). Supersedes NE/SA/SE5521 of 1994 Aug 31.** Engineering Change Notice 853–0043 29139 (date: 20021101). **Modifications:** • Delete SE5521 and ceramic package options.
_1	19940831	**Product data; initial version.** Engineering Change Notice 853–0043 13721 (date: 19940831).

LVDT signal conditioner NE/SA5521

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Level	Data sheet status [1]	Product status [2] [3]	Definitions
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